HIGH-SPEED 2.5V 707 512/256/128K X 18 SYNCHRONOUS DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

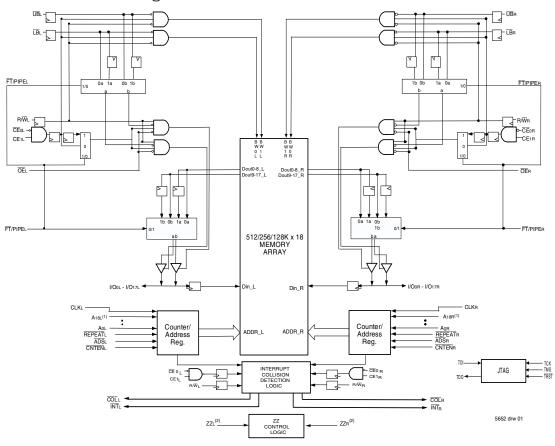
70T3339/19/99S

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 3.4 (200MHz)/3.6ns (166MHz)/ 4.2ns (133MHz)(max.)
 - Industrial: 4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Interrupt and Collision Detection Flags
- Full synchronous operation on both ports
 - 5ns cycle time, 200MHz operation (14Gbps bandwidth)
 - Fast 3.4ns clock to data out
 - Data input, address, byte enable and control registers

Functional Block Diagram

- 1.5ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 200MHz
- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output Mode
- 2.5V (±100mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- Industrial temperature range (-40°C to +85°C) is available at 133MHz
- Available in a 256-pin Ball Grid Array (BGA) and 208-pin fine pitch Ball Grid Array (fpBGA)
- Supports JTAG features compliant with IEEE 1149.1
- Green parts available, see ordering information



NOTES:

- 1. Address A18 is a NC for the IDT70T3319. Also, Addresses A18 and A17 are NC's for the IDT70T3399.
- 2. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode.

NOVEMBER 2019

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70T3339/19/99 is a high-speed 512/256/128k x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70T3339/19/99 has been optimized for applications having unidirec-

tional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT70T3339/19/99 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) is at 2.5V.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Pin Configuration (3,4,5,6)

70T3339/19/99 BC256⁽⁸⁾ BCG256⁽⁸⁾ 256-Pin BGA Top View

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	A17L ⁽²⁾	A14L	A11L	A8L	NC	CE1L	OEL		A5L	A2L	AOL	NC	NC
B1	B2	^{B3}	B4	B5	B6	B7	B8	B9	^{B10}	B11	B12	B13	B14	B15	^{B16}
INTL	NC	TDO	A18L ⁽¹⁾	A15L	A12L	A9L	UBL	CE0L	R/₩L	REPEAT∟	A4L	A1L	Vdd	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	^{C11}	C12	С13	C14	C15	C16
COLL	I/O9L	Vss	A16L	A13L	A10L	A7L	NC	TBL	CLK∟	ADS∟	A6L	Аз∟	OPT∟	NC	I/O8L
D1	d2	D3	D4	d5	d6	d7	d8	d9	d10	d11	d12	D13	D14	D15	D16
NC	I/O9r	NC	PIPE/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	NC	NC	I/O8R
e1	e2	E3	e4	e5	e6	^{E7} NC	E8	^{E9}	E10	e11	e12	e13	E14	e15	e16
I/O10r	I/O10L	NC	Vddql	Vdd	Vdd		Vss	Vss	Vss	Vdd	Vdd	Vddqr	NC	I/O7l	I/O7r
f1	F2	f3	f4	f5	F6	F7	^{F8}	^{F9}	F10	F11	F12	f13	f14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	NC	NC	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6r	NC	I/O6L
G1	G2	G3	G4	G5	G6	G7	G8	G9	G10	G11	G12	g13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O5L	NC	NC
H1	h2	H3	h4	H5	H6	H7	H8	H9	H10	H11	H12	h13	H14	H15	h16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5r
J1	J2	j3	j4	J5	J6	J7	_{J8}	^{J9}	J10	J11	J12	j13	J14	J15	J16
I∕O13∟	I/O14R	I/O13R	Vddql	ZZR	Vss	Vss	Vss	Vss	Vss	Vss	ZZ L	Vddqr	I/O4r	I/Озг	I/O4L
кı	K2	k3	k4	K5	K6	к7	K8	к9	K10	K11	K12	k13	K14	K15	к16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	І/Оз∟
l1	L2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	L15	l16
I/O15L	NC	I/O15R	Vddqr	Vdd	NC	NC	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2l	NC	I/O2R
M1	m2	M3	M4	M5	M6	M7	M8	M9	M10	M11	M12	M13	^{M14}	м15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	Vdd	NC	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O1R	I/O1L	NC
N1	N2	N3	№	n5	N6	n7	n8	^{N9}	n10	N11	n12	N13	N14	N15	N16
NC	I/O17R	NC	PIPE/FTR	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	NC	I/Oor	NC
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	^{p11}	P12	P13	P14	P15	Р16
COLR	I/O17L	TMS	A16R	A13R	A10R	A7R	NC	TBR	CLKR	ADSr	A 6R	A 3R	NC	NC	I/Ool
rı	R2	^{R3}	R4	R5	R6	R7	r8	^{R9}	R10	r11	R12	R13	^{R14}	R15	^{R16}
INTr	NC	TRST	A18R ⁽¹⁾	A15R	A12R	A 9R	UBr	CE0R	R∕W R	REPEATR	A 4R	A 1R	OPTR	NC	NC
T1	T2	тз	T4	T5	т6	T7	T8	^{T9}	T10	t11	T12	T13	T14	T15	^{т16}
NC	TCK	NC	A 17R ⁽²⁾	A 14R	А 11R	A8R	NC	CE1R	OEr	CNTENR	A 5R	A 2R	A 0R	NC	NC

NOTES:

1. Pin is a NC for IDT70T3319 and IDT70T3399.

2. Pin is a NC for IDT70T3399.

3. All VDD pins must be connected to 2.5V power supply.

 All VDDD pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).

5. All Vss pins must be connected to ground supply.

6. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.

7. This package code is used to reference the package diagram.

8. This text does not indicate orientation of the actual part-marking.

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70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Pin Configurations(con't)^(3,4,5,6)

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	_
I/O9L	INTL	Vss	TDO	NC	A16L	A12L	A8L	NC	Vdd	CLK∟	CNTEN L	A4L	Aol	OPT∟	NC	Vss	A
NC	Vss	COLL	TDI	A _{17L} (2)	A13L	A9L	NC		Vss	ADSL	A5L	A1L	NC	VDDQR	I/O8L	NC	в
VDDQL	I/O9R	VDDQR	PIPE/FTL	A _{18L} (1)	A14L	A10L	Ū₿∟	CE1L	Vss	R/WL	A6L	A2L	Vdd	I/O8R	NC	Vss	С
NC	Vss	I/O10L	NC	A15L	A11L	A7L	LΒL	Vdd	ŌĒL	REPEATL	A3L	Vdd	NC	Vddql	I/O7L	I/O7r	D
I/O11L	NC	Vddqr	I/O10R						-				I/O6L	NC	Vss	NC	E
VDDQL	I/O11R	NC	Vss										Vss	I/O6r	NC	Vddqr	F
NC	Vss	I/O12L	NC										NC	VDDQL	I/O5l	NC	G
VDD	NC	Vddqr	I/O12R					3339/ F208		9			Vdd	NC	Vss	I/O5r	н
VDDQL	Vdd	Vss	ZZR		BEG208 ⁽⁷⁾								ZZ∟	VDD	Vss	Vddqr	J
I/O14R	Vss	I/O13R	Vss					p Vie					I/O3r	VDDQL	I/O4r	Vss	К
NC	I/O14L	Vddqr	I/O13L										NC	I/O3L	Vss	I/O4L	L
VDDQL	NC	I/O15R	Vss										Vss	NC	I/O2r	Vddqr	M
NC	Vss	NC	I/O15L										I/O1r	Vddql	NC	I/O2L	Ν
I/O16R	I/O16L	Vddqr	COLR	TRST	A16R	A12R	A8R	NC	Vdd	CLKR	CNTEN R	A4R	NC	I/O1L	Vss	NC	Р
Vss	NC	I/O17R	тск	A _{17R} ⁽²⁾	A13R	A9R	NC	CEOR	Vss	ADSR	A5R	A1R	NC	VDDQL	I/Oor	Vddqr	R
NC	I/O17L	Vddql	TMS	A _{18R} ⁽¹⁾	A14R	A10R	ŪBr	CE1R	Vss	R/WR	Agr	A2R	Vss	NC	Vss	NC	Т
Vss	ĪNTR	PIPE/FT _R	NC	A15R	A11R	A7R	LBR	Vdd	ŌĒr	REPEATR	Азк	Aor	Vdd	OPT R	NC	I/Ool	U

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NOTES:

- 1. Pin is a NC for IDT70T3319 and IDT70T3399.
- 2. Pin is a NC for IDT70T3399.
- 3. All VDD pins must be connected to 2.5V power supply.
- 4. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).
- 5. All Vss pins must be connected to ground supply.
- 6. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 7. This package code is used to reference the package diagram.
- 8. This text does not indicate orientation of the actual part-marking.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Pin Names

Left Port	Right Port	Names						
CEOL, CE1L	CEOR, CE1R	Chip Enables (Input) ⁽⁶⁾						
R/WL	R/WR	Read/Write Enable (Input)						
ŌĒL	ŌĒr	Output Enable (Input)						
Aol - A18L ⁽⁵⁾	Aor - A18R ⁽⁵⁾	Address (Input)						
1/Ool - 1/O17L	1/O0r - 1/O17r	Data Input/Output						
CLKL	CLKR	Clock (Input)						
PL/FTL	PL/ FT r	Pipeline/Flow-Through (Input)						
ADSL	ADSR	Address Strobe Enable (Input)						
		Counter Enable (Input)						
REPEATL	REPEATR	Counter Repeat ⁽³⁾						
UBL	ŪBR	Upper Byte Enable (I/O9 - I/O17) ⁽⁶⁾						
LB L	LB R	Lower Byte Enable (I/Oo - I/O8) ⁽⁶⁾						
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾ (Input)						
OPT∟	OPTR	Option for selecting VDDQx ^(1,2) (Input)						
ZZL	ZZR	Sleep Mode pin ⁽⁴⁾ (Input)						
V	/DD	Power (2.5V) ⁽¹⁾ (Input)						
V	'ss	Ground (OV) (Input)						
٢	īdi	Test Data Input						
٢	īdi	Test Data Output						
Т	СК	Test Logic Clock (10MHz) (Input)						
П	MS	Test Mode Select (Input)						
T	RST	Reset (Initialize TAP Controller) (Input)						
INTL	INT R	Interrupt Flag (Output)						
	COLR	Collision Alert (Output)						

5652 tbl 01

Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VDD (2.5V), then that port's I/Os and controls will operate at 3.3V levels and VDDDx must be supplied at 3.3V. If OPTx is set to Vss (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDDDx must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.
- 3. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS x.
- 4. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. It is recommended that boundary scan not be operated during sleep mode.
- Address A18x is a NC for the IDT70T3319. Also, Addresses A18x and A17x are NC's for the IDT70T3399.
- Chip Enables and Byte Enables are double buffered when PL/FT = ViH, i.e., the signals take two cycles to deselect.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

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Industrial and Commercial Temperature Ranges

Trut	<u>h Tak</u>	<u>ple I–</u>	-Rea	<u>ad/Wr</u>	<u>ite a</u>	<u>ind E</u>	nabl	<u>e Contro</u>	ol ^(1,2,3,4)	
ŌĒ	CLK	<u>C</u> E₀	CE1	ŪB	LB	R/W	ZZ	Upper Byte I/O9-17	Lower Byte I/Oo-8	MODE
Х	↑	Н	Х	Х	Х	Х	L	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	Х	L	Х	Х	Х	L	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	L	Н	Н	Н	Х	L	High-Z	High-Z	Both Bytes Deselected
Х	Ŷ	L	Н	Н	L	L	L	High-Z	Din	Write to Lower Byte Only
Х	Ŷ	L	Н	L	Н	L	L	Din	High-Z	Write to Upper Byte Only
Х	Ŷ	L	Н	L	L	L	L	Din	Din	Write to Both Bytes
L	Ŷ	L	Н	Н	L	Н	L	High-Z	Dout	Read Lower Byte Only
L	Ŷ	L	Н	L	Н	Н	L	Dout	High-Z	Read Upper Byte Only
L	Ŷ	L	Н	L	L	Н	L	Dout	Dout	Read Both Bytes
Н	Ŷ	L	Н	L	L	Х	L	High-Z	High-Z	Outputs Disabled
Х	Х	Х	Х	Х	Х	Х	Н	High-Z	High-Z	Sleep Mode

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NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.

3. $\overline{\text{OE}}$ and ZZ are asynchronous input signals.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

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Truth Table II—Address Counter Control (1,2)

Address	Previous Internal Address	Internal Address Used	CLK	ADS		REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	х	Н	Di/o (n)	External Address Used
Х	An	An + 1	Ŷ	Н	L ⁽⁵⁾	Н	Di/o(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	\uparrow	Н	Н	Н	Di/o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	Ŷ	Х	Х	L ⁽⁴⁾	Di/o(n)	Counter Set to last valid ADS load
NOTEC								5652 tbl 03

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CE0, CE1, UB, LB and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CEo, CE1, UB and LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, UB and LB.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	2.5V <u>+</u> 100mV
Industrial	-40°C to +85°C	0V	2.5V <u>+</u> 100mV
			5652 tbl 04

NOTE:

1. This is the parameter TA. This is the "instant on" case temperature.

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Vss	Ground	0	0	0	V
Vін	Input High Volltage (Address, Control & Data I/O Inputs) ⁽³⁾	1.7		Vddq + 100mV ⁽²⁾	V
ViH	Input High Voltage - JTAG	1.7		Vdd + 100mV ⁽²⁾	V
VIH	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		VDD + 100mV ⁽²⁾	V
Vı∟	Input Low Voltage	-0.3 ⁽¹⁾		0.7	V
VIL	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	V

Recommended DC Operating Conditions with VDD0 at 2.5V

NOTES:

1. VIL (min.) = -1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to Vss(0V), and VDDOX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDO at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
Vih	Input High Voltage (Address, Control &Data I/O Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	v
Vін	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	v
Vih	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		VDD + 100mV ⁽²⁾	v
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.8	V
Vı∟	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	v

NOTES:

1. VIL (min.) = -1.0V for pulse width less than tcyc/2, or 5ns, whichever is less.

5652 tbl 05b

2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

 To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VDD (2.5V), and VDDOX for that port must be supplied as indicated above.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm (Vdd)	VDD Terminal Voltage with Respect to GND	-0.5 to 3.6	V
Vterm ⁽²⁾ (Vddq)	VDDQ Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
V _{TERM⁽²⁾ (INPUTS and I/O's)}	Input and I/O Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
Tbias ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	٥C
ЛЛ	Junction Temperature	+150	٥C
IOUT(For VDDQ = 3.3V)	DC Output Current	50	mA
IOUT(For VDDQ = 2.5V)	DC Output Current	40	mA
	-		5652 tbl 06

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any Input or I/O pin cannot exceed VDDQ during power supply ramp up.
- 3. Ambient Temperature under DC Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

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(TA = +25°C, f = 1.0MHz) PQFP ONLY
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Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF
				5652 tbl 07

NOTES:

- 1. These parameters are determined by device characterization, but are not production tested.
- 2. 3dV references the interpolated capacitance when the input and output switch from OV to 3V or from 3V to OV.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 2.5V ± 100mV)

			70T3339	/19/99S	
Symbol	Parameter	Test Conditions	Min.	Мах.	Unit
Lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ		10	μA
Lu	JTAG & ZZ Input Leakage Current ^(1,2)	$V_{DD} = Max., V_{IN} = 0V to V_{DD}$		±30	μA
ILO	Output Leakage Current ^(1,3)	$\overline{CE}_0 = VIH \text{ or } CE_1 = VIL, VOUT = 0V \text{ to } VDDQ$		10	μA
Vol (3.3V)	Output Low Voltage ⁽¹⁾	Iol = +4mA, Vdda = Min.		0.4	V
Voн (3.3V)	Output High Voltage ⁽¹⁾	Ioh = -4mA, VDDQ = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽¹⁾	Iol = +2mA, Vdda = Min.		0.4	V
Voн (2.5V)	Output High Voltage ⁽¹⁾	Ioh = -2mA, VDDQ = Min.	2.0		V

NOTES:

1. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.6 for details.

2. Applicable only for TMS, TDI and TRST inputs.

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3. Outputs tested in tri-state mode.

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}(V_{DD} = 2.5V \pm 100 \text{mV})$

					S2	9/19/99 00 Only ⁽⁷⁾	S1 Co	9/19/99 66 m'l Ind	S1 Co	9/19/99 33 m' nd	
Symbol	Parameter	Test Condition	Versio	n	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Uni
IDD	Dynamic Operating	\overline{CE}_{L} and $\overline{CE}_{R}=VIL$,	COM'L	S	375	525	320	450	260	370	
	Current (Both Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S		_	320	510	260	450	m/
ISB1 ⁽⁶⁾	Standby Current	$\overline{CE}L = \overline{CER} = VIH$	COM'L	S	205	270	175	230	140	190	
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S		_	175	275	140	235	m,
ISB2 ⁽⁶⁾	Standby Current	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	300	375	250	325	200	250	
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	_	_	250	365	200	310	m
ISB3	Full Standby Current	Both Ports CEL and	COM'L	S	5	15	5	15	5	15	
	(Both Ports - CMOS Level Inputs)	$\label{eq:certain} \begin{split} \overline{CE} R &\geq V \text{DDQ} - 0.2 \text{V}, \text{ VIN} \geq V \text{DDQ} - 0.2 \text{V} \\ \text{or VIN} &\leq 0.2 \text{V}, \text{ f} = 0^{(2)} \end{split}$	IND	S			5	20	5	20	m.
ISB4 ⁽⁶⁾	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$	COM'L	S	300	375	250	325	200	250	
	(One Port - CMOS Level Inputs)	$\label{eq:VIN_expansion} \begin{array}{l} \text{VIN} \geq \text{VDDQ} \ \text{-} \ 0.2 \text{V} \ \text{or} \ \text{VIN} \leq 0.2 \text{V} \\ \text{Active Port, Outputs Disabled, } f = f\text{MAX}^{(1)} \end{array}$	IND	S	_	_	250	365	200	310	m.
lzz	Sleep Mode Current	ZZL = ZZR = VIH f=fMAX ⁽¹⁾	COM'L	S	5	15	5	15	5	15	
	(Both Ports - TTL Level Inputs)	I=IMAX''	IND	S	_	_	5	20	5	20	m

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS".

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 2.5V, $TA = 25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 15mA (Typ).

5. $\overline{CE}x = VIL$ means $\overline{CE}ox = VIL$ and CE1x = VIH

 $\overline{CE}x = VIH$ means $\overline{CE}ox = VIH$ or CE1x = VIL

 $\overline{\text{CE}}x \leq 0.2V$ means $\overline{\text{CE}}\textsc{ox} \leq \underline{0.2}V$ and $\text{CE}\textsc{ix} \geq \text{VDDQ}$ - 0.2V

 $\overline{\text{CE}}\text{x} \geq \text{V}\text{DDQ}$ - 0.2V means $\overline{\text{CE}}\text{ox} \geq \text{V}\text{DDQ}$ - 0.2V or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.

6. IsB1, ISB2 and ISB4 will all reach full standby levels (ISB3) on the appropriate port(s) if ZZL and/or ZZR = VIH.

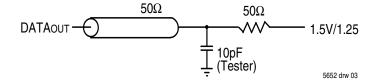
7. 200Mhz is not available in the BF-208 package.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

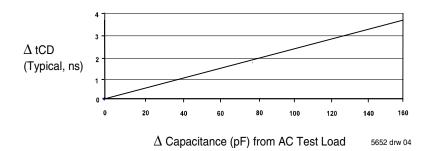
AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	1.5V/1.25V
Output Reference Levels	1.5V/1.25V
Output Load	Figures 1 and 2









70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) (2,3) (VDD = 2.5V ± 100mV, TA = 0°C to +70°C)

	and Write Cycle Timing) ^(2,3) (v	70T33	39/19/99 200 Only ⁽⁴⁾	70T333 S1 Co	89/19/99 166 om'l Ind	70T3339/19/99 S133 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	15	—	20		25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	5	—	6		7.5		ns
tcн1	Clock High Time (Flow-Through) ⁽¹⁾	6		8		10		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	6	—	8		10	—	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2	—	2.4		3	—	ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2	—	2.4		3	—	ns
tsa	Address Setup Time	1.5	—	1.7		1.8	—	ns
tha	Address Hold Time	0.5	—	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.5		1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5		0.5		0.5		ns
tsв	Byte Enable Setup Time	1.5		1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5		0.5		0.5		ns
tsw	R/W Setup Time	1.5	—	1.7		1.8		ns
tHW	R/W Hold Time	0.5	—	0.5		0.5		ns
tsp	Input Data Setup Time	1.5	—	1.7		1.8		ns
thd	Input Data Hold Time	0.5	—	0.5		0.5		ns
tsad	ADS Setup Time	1.5	_	1.7		1.8		ns
thad	ADS Hold Time	0.5	_	0.5		0.5		ns
tscn	CNTEN Setup Time	1.5		1.7		1.8		ns
then	CNTEN Hold Time	0.5		0.5		0.5		ns
İ SRPT	REPEAT Setup Time	1.5		1.7		1.8		ns
t HRPT	REPEAT Hold Time	0.5		0.5		0.5		ns
toe	Output Enable to Data Valid		4.4		4.4		4.6	ns
tolz ⁽⁵⁾	Output Enable to Output Low-Z	1		1		1		ns
tohz ⁽⁵⁾	Output Enable to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		10		12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾	—	3.4		3.6		4.2	ns
tDC	Data Output Hold After Clock High	1		1		1		ns
tскнz ⁽⁵⁾	Clock High to Output High-Z	1	3.4	1	3.6	1	4.2	ns
tcklz ⁽⁵⁾	Clock High to Output Low-Z	1		1		1		ns
tins	Interrupt Flag Set Time		7		7		7	ns
tinr	Interrupt Flag Reset Time		7		7		7	ns
tcols	Collision Flag Set Time	—	3.4		3.6		4.2	ns
t COLR	Collision Flag Reset Time	—	3.4		3.6		4.2	ns
tzzsc	Sleep Mode Set Cycles	2	-	2		2		cycles
tzzrc	Sleep Mode Recovery Cycles	3	-	3		3		cycles
Port-to-Port D	Delay			•	•			
tco	Clock-to-Clock Offset	4		5		6		ns
tofs	Clock-to-Clock Offset for Collision Detection	Please r	efer to Coll	ision Dete	tion Timin	n Table or	Page 20	

5652 tbl 11

NOTES:

1. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when FT/PIPEx = Vbb (2.5V). Flow-through parameters (tcvc1, tcb1) apply when FT/PIPE = Vss (0V) for that port.

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPE and OPT. FT/PIPE and OPT should be treated as DC signals, i.e. steady state during operation.

3. These values are valid for either level of VDDa (3.3V/2.5V). See page 5 for details on selecting the desired operating voltage levels for each port.

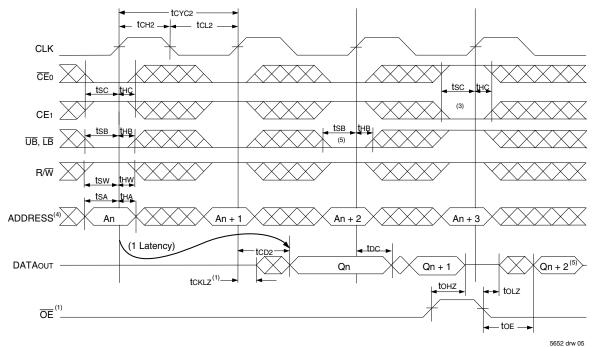
4. 200Mhz is not available in BF-208 package.

5. Guaranteed by design (not production tested).

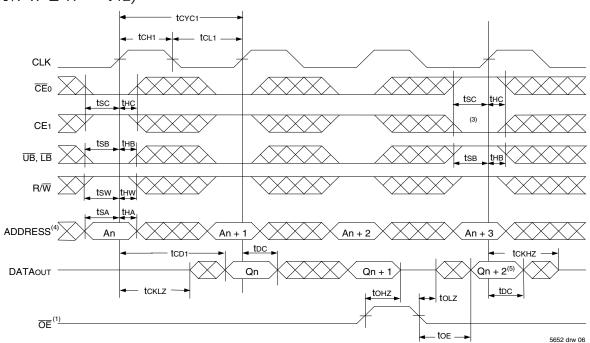
70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE'x' = VIH)^{(2)}$



Timing Waveform of Read Cycle for Flow-through Output $(\mathbf{FT}/PIPE^*X^* = VIL)^{(2,6)}$



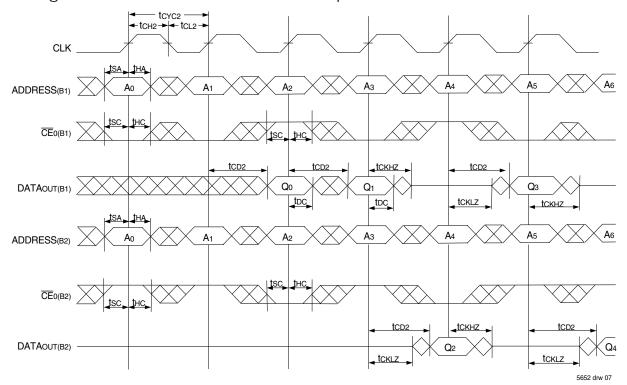
NOTES:

- 1. DE is asynchronously controlled; all other inputs depicted in the above waveforms are synchronous to the rising clock edge.
- 2. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{REPEAT} = VIH$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $\overline{CE}_1 = V_{IL}$, \overline{UB} , $\overline{LB} = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If UB, LB was HIGH, then the appropriate Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.

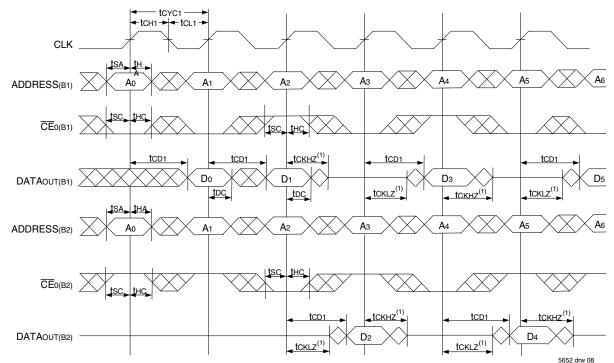
70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of a Multi-Device Pipelined Read^(1,2)



Timing Waveform of a Multi-Device Flow-Through Read^(1,2)



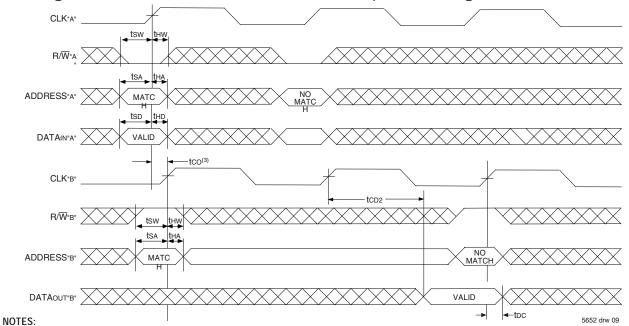
NOTES:

1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70T3339/19/99 for this waveform,

- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{REPEAT} = VIH.

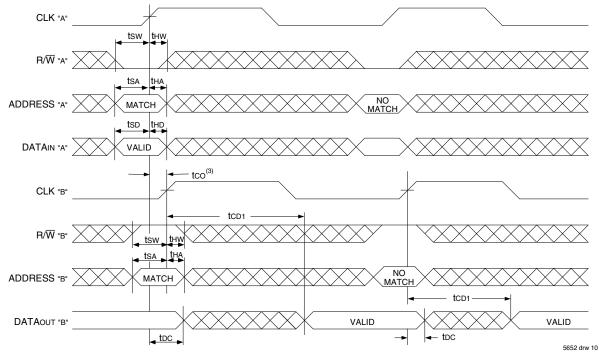
70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2,4)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,4)



NOTES:

- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.
- 2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcp1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

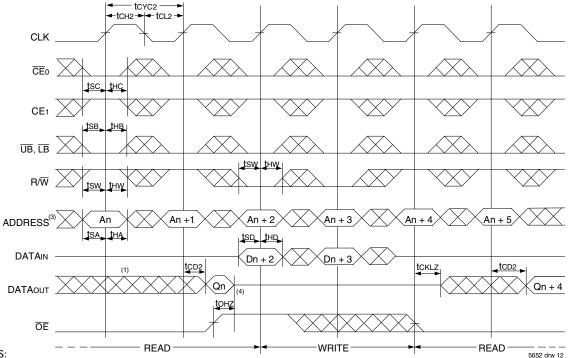
14

Timing Waveform of Pipelined Read-to-Write-to-Read $(\overline{OE} = VIL)^{(2)}$ tCYC2 -tCH2-→| CLK **CE**0 tsc, thc CE1 ţsв UB, LB tsw R/W tsw ADDRESS⁽³⁾ An ٩n An An +1 An + 2 An + 2 ISA, THA tsp **THD** DATAIN Dn + 2 tCD2 tCD2 (1) tскнz tCKLZ DATAOUT Qn Qn + 3 NOP⁽⁴⁾ WRITE READ READ 5652 drw 11

NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH. "NOP" is "No Operation".
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

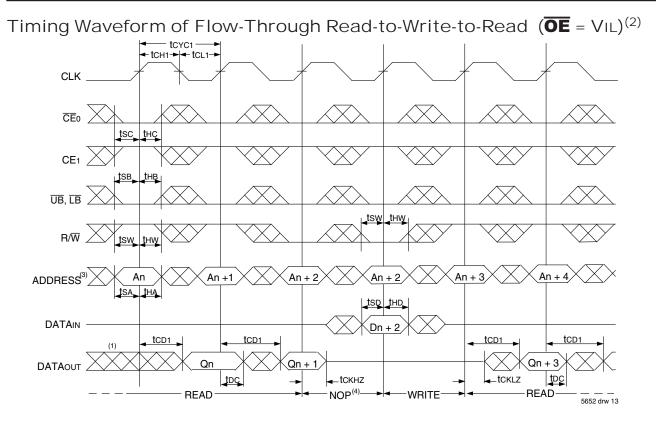
2. CEO, UB, LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

^{1.} Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

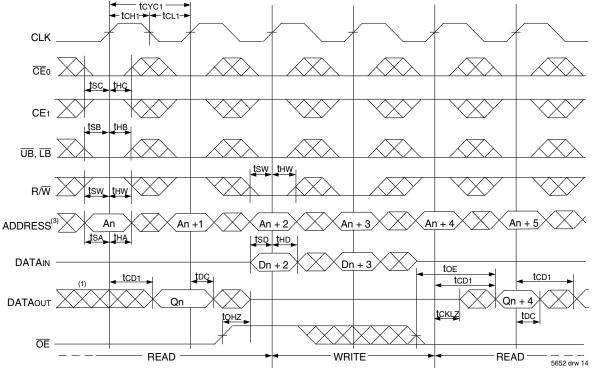
^{3.} Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

^{4.} This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM



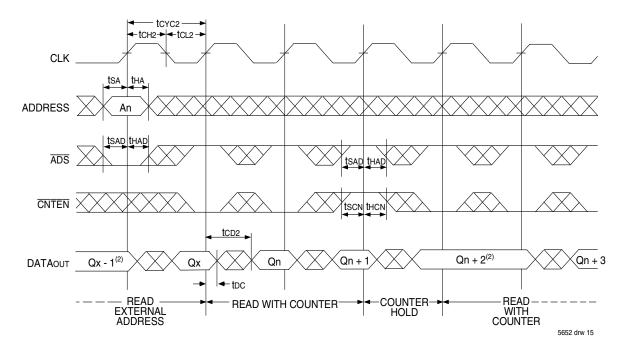
Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



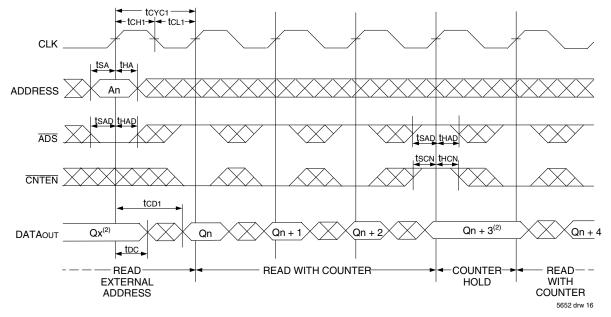
NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.
- 3. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



 $Timing \, Waveform \, of \, Flow-Through \, Read \, with \, Address \, Counter \, Advance^{(1)}$

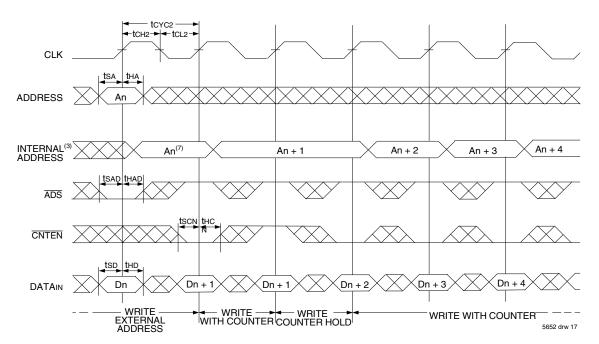


NOTES:

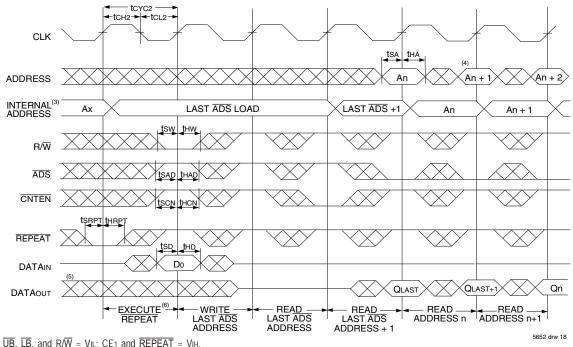
2. If there is no address change via $\overline{\text{ADS}}$ = VIL (loading a new address) or $\overline{\text{CNTEN}}$ = VIL (advancing the address), i.e. $\overline{\text{ADS}}$ = VIH and $\overline{\text{CNTEN}}$ = VIH, then the data output remains constant for subsequent clocks.

^{1.} \overline{CE}_{0} , \overline{OE} , \overline{UB} , \overline{LB} = VIL; CE1, R/W, and \overline{REPEAT} = VIH.

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



Timing Waveform of Counter Repeat⁽²⁾

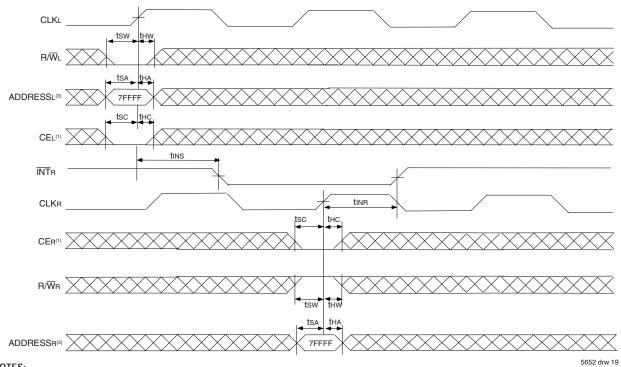


NOTES:

- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = VIL$; CE_1 and $\overline{REPEAT} = VIH$.
- 2. \overline{CE}_{0} , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIL.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid 6. ADS load will be accessed. Extra cycles are shown here simply for clarification. For more information on REPEAT function refer to Truth Table II.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

5652 tbl 12

Waveform of Interrupt Timing (2)



NOTES:

- 1. $\overline{CE}_0 = VIL \text{ and } CE_1 = VIH$
- 2. All timing is the same for Left and Right ports.
- 3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

	Left Port									
CLKL	R/WL ⁽²⁾	CEL ⁽²⁾	A18L-A0L ^(3,4,5)	ĪNTL	CLKr	R/ W R ⁽²⁾	CER ⁽²⁾	A18R-A0R ^(3,4,5)	ĪNTR	Function
Ŷ	L	L	7FFFF	Х	Ŷ	Х	Х	Х	L	Set Right INTR Flag
Ŷ	Х	Х	Х	Х	Ŷ	Н	L	7FFFF	Н	Reset Right INTR Flag
Ŷ	Х	Х	Х	L	Ŷ	L	L	7FFFE	Х	Set Left INTL Flag
↑	Н	L	7FFFE	Н	Ŷ	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table III — Interrupt Flag⁽¹⁾

NOTES:

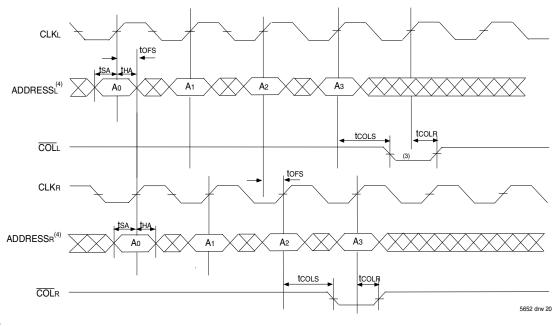
1. \overline{INT}_L and \overline{INT}_R must be initialized at power-up by Resetting the flags.

2. CE0 = VIL and CE1 = VIH. RW and CE are synchronous with respect to the clock and need valid set-up and hold times.

- 3. A18x is a NC for IDT70T3319, therefore Interrupt Addresses are 3FFFF and 3FFFE.
- 4. A18x and A17x are NC's for IDT70T3399, therefore Interrupt Addresses are 1FFFF and 1FFFE.
- 5. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Waveform of Collision Timing (1,2) Both Ports Writing with Left Port Clock Leading



NOTES:

1. $\overline{CE}_0 = V_{IL}, CE_1 = V_{IH}.$

- 2. For reading port, OE is a Don't care on the Collision Detection Logic. Please refer to Truth Table IV for specific cases.
- 3. Leading Port Output flag might output 3tcyc2 + tcoLs after Address match.
- 4. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

Cualo Timo	tors (ns)				
Cycle Time	Region 1 (ns) ⁽¹⁾	Region 2 (ns) ⁽²⁾			
5ns	0 - 2.8	2.81 - 4.6			
6ns	0 - 3.8	3.81 - 5.6			
7.5ns	0 - 5.3	5.31 - 7.1			

Collision Detection Timing^(3,4)

5652 tbl 13

NOTES:

1. Region 1

Both ports show collision after 2nd cycle for Addresses 0, 2, 4 etc. 2. Region 2

Leading port shows collision after 3rd cycle for addresses 0, 3, 6, etc. while trailing port shows collision after 2nd cycle for addresses 0, 2, 4 etc.

- 3. All the production units are tested to midpoint of each region.
- 4. These ranges are based on characterization of a typical device.

Truth Table IV — Collision Detection Flag

Left Port					Right Port					
CLKL	R/ W L ⁽¹⁾	CEL ⁽¹⁾	A18L-A0L ⁽²⁾		CLKr	R/ W R ⁽¹⁾	CER ⁽¹⁾	A18R-A0R ⁽²⁾	COLR	Function
Ŷ	Н	L	MATCH	Н	Ŷ	Н	L	MATCH	Н	Both ports reading. Not a valid collision. No flag output on either port.
Ŷ	Н	L	MATCH	L	Ŷ	L	L	MATCH	Н	Left port reading, Right port writing. Valid collision, flag output on Left port.
Ŷ	L	L	MATCH	Н	Ŷ	Н	L	MATCH	L	Right port reading, Left port writing. Valid collision, flag output on Right port.
Ŷ	L	L	MATCH	L	Ŷ	L	L	MATCH	L	Both ports writing. Valid collision. Flag output on both ports.

NOTES:

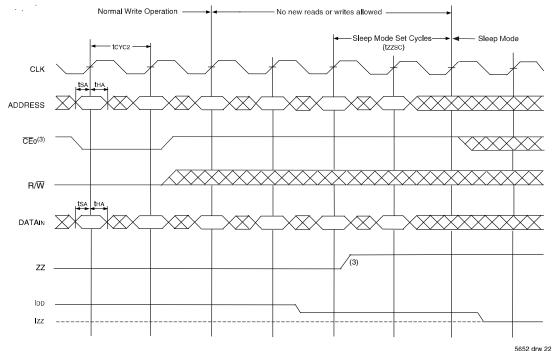
1. CE0 = VIL and CE1 = VIH. R/W and CE are synchronous with respect to the clock and need valid set-up and hold times.

2. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

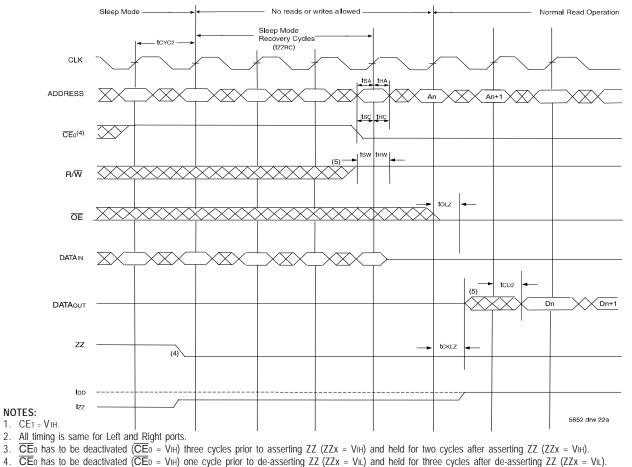
70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform - Entering Sleep Mode (1,2)



Timing Waveform - Exiting Sleep Mode (1,2)



^{5.} The device must be in Read Mode (R/W High) when exiting sleep mode. Outputs are active but data is not valid until the following cycle.

3.

Industrial and Commercial Temperature Ranges

Functional Description

The IDT70T3339/19/99 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse width is independent of the cycle time.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70T3339/19/99s for depth expansion configurations. Two cycles are required with \overline{CE} o LOW and CE1 HIGH to reactivate the outputs.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (INTL) is asserted when the right port writes to memory location 7FFFE (HEX), where a write is defined as $\overline{CE}R = R/\overline{W}R = VIL$ per the Truth Table. The left port clears the interrupt through access of address location 7FFFE when $\overline{CE}L = VIL$ and $R/\overline{W}L = VIH$. Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FFFF (HEX) and to clear the interrupt flag (INTR), the right port must read the memory location 7FFFF (3FFFF or 3FFFE for IDT70T3319 and 1FFFF or 1FFFE for IDT70T3399). The message (18 bits) at 7FFFE or 7FFFF (3FFFF or 3FFFE for IDT70T3319 and 1FFFF or 1FFFE for IDT70T3399) is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 7FFFE and 7FFFF (3FFFF or 3FFFE for IDT70T3319 and 1FFFF or 1FFFE for IDT70T3399) are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Collision Detection

Collision is defined as an overlap in access between the two ports resulting in the potential for either reading or writing incorrect data to a specific address. For the specific cases: (a) Both ports reading - no data is corrupted, lost, or incorrectly output, so no collision flag is output on either port. (b) One port writing, the other port reading - the end result of the write will still be valid. However, the reading port might capture data that is in a state of transition and hence the reading port's collision flag is output. (c) Both ports writing - there is a risk that the two ports will interfere with each other, and the data stored in memory will not be a valid write from either port (it may essentially be a random combination of the two). Therefore, the collision flag is output on both ports. Please refer to Truth Table IV for all of the above cases.

The alert flag (COL_x) is asserted on the 2nd or 3rd rising clock edge of the affected port following the collision, and remains low for one cycle. Please refer to Collision Detection Timing table on page 20. During that next cycle, the internal arbitration is engaged in resetting the alert flag (this avoids a specific requirement on the part of the user to reset the alert flag). If two collisions occur on subsequent clock cycles, the second collision may not generate the appropriate alert flag. A third collision will generate the alert flag as appropriate. In the event that a user initiates a burst access on both ports with the same starting address on both ports and one or both ports writing during each access (i.e., imposes a long string of collisions on contiguous clock cycles), the alert flag will be asserted and cleared every other cycle. Please refer to the Collision Detection Timing waveform on page 20.

Collision detection on the IDT70T3339/19/99 represents a significant advance in functionality over current sync multi-ports, which have no such capability. In addition to this functionality the IDT70T3339/19/99 sustains the keyfeatures of bandwidth and flexibility. The collision detection function is very useful in the case of bursting data, or a string of accesses made to sequential addresses, in that it indicates a problem within the burst, giving the user the option of either repeating the burst or continuing to watch the alert flag to see whether the number of collisions increases above an acceptable threshold value. Offering this function on chip also allows users to reduce their need for arbitration circuits, typically done in CPLD's or FPGA's. This reduces board space and design complexity, and gives the user more flexibility in developing a solution.

Sleep Mode

The IDT70T3339/19/99 is equipped with an optional sleep or low power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode.

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZx = VIH) and three cycles after de-asserting ZZ (ZZx = VIL), the device must be disabled via the chip enable pins. If a write or read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode (R/Wx = VIH) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue torun without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

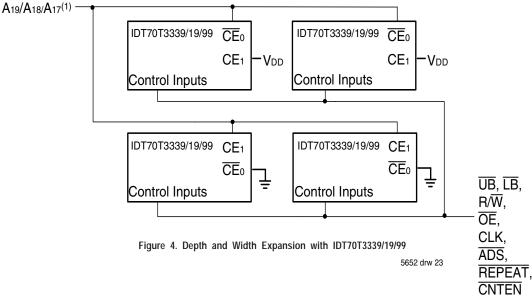
70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

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Depth and Width Expansion

The IDT70T3339/19/99 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

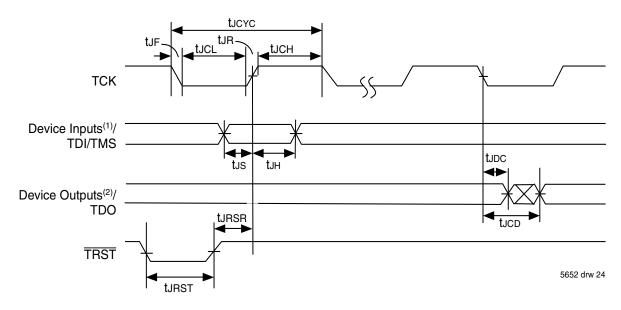
The IDT70T3339/19/99 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.



NOTE:

1. A19 is for IDT70T3339, A18 is for IDT70T3319, A17 is for IDT70T3399.

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, and TRST.

2. Device outputs = All device outputs except TDO.

		70T3		
Symbol	Parameter	Min.	Мах.	Units
ticyc	JTAG Clock Input Period	100		ns
рсн	JTAG Clock HIGH	40		ns
tici	JTAG Clock Low	40		ns
tur	JTAG Clock Rise Time		3(1)	ns
IJF	JTAG Clock Fall Time		3(1)	ns
URST	JTAG Reset	50		ns
URSR	JTAG Reset Recovery	50		ns
tico	JTAG Data Output		25	ns
tudc	JTAG Data Output Hold	0		ns
tıs	JTAG Setup	15		ns
Uн	JTAG Hold	15		ns

JTAG AC Electrical <u>Charac</u>teristics^(1,2,3,4)

NOTES:

- 1. Guaranteed by design.
- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

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Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x333 ⁽¹⁾	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

NOTE:

1. Device ID for IDT70T3319 is 0x334. Device ID for IDT70T3399 is 0x335.

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5652 tbl 17

System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state except COLx & INTx outputs.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	0101, 0111, 1000, 1001, 1010, 1011, 1100	Several combinations are reserved. Do not use codes other than those identified above.
PRIVATE	0110,1110,1101	For internal use only.

NOTES:

1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.

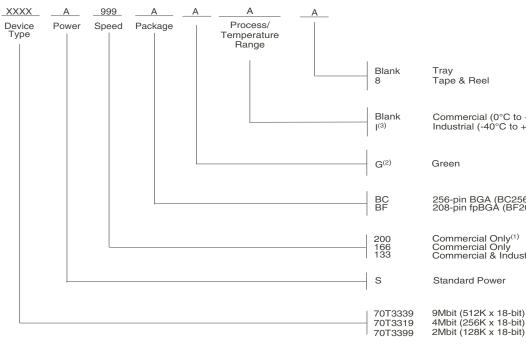
3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

5652 tbl 18

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Ordering Information



Tray Tape & Reel Commercial (0°C to +70°C) Industrial (-40°C to +85°C) Green 256-pin BGA (BC256, BCG256) 208-pin fpBGA (BF208, BFG208) Commercial Only⁽¹⁾ Commercial Only⁽¹⁾ Commercial Only Commercial Only Speed in Megahertz Standard Power

9Mbit (512K x 18-bit) Synchronous Dual-Port RAM 4Mbit (256K x 18-bit) Synchronous Dual-Port RAM 2Mbit (128K x 18-bit) Synchronous Dual-Port RAM

5652 drw 25

NOTES:

- 1. 200Mhz is not available in the BF-208 package.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.
- 3. Contact your local sales office for industrial temp range for other speeds, packages and powers.

Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade	Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70T3319S133BC	BC256	CABGA	С	133	70T3339S133BC	BC256	CABGA	С
	70T3319S133BC8	BC256	CABGA	С		70T3339S133BC8	BC256	CABGA	С
	70T3319S133BF	BF208	CABGA	С		70T3339S133BCI	BC256	CABGA	I
	70T3319S133BF8	BF208	CABGA	С		70T3339S133BCI8	BC256	CABGA	I
	70T3319S133BFGI	BFG208	CABGA	I		70T3339S133BF	BF208	CABGA	С
	70T3319S133BFGI8	BFG208	CABGA	Ι		70T3339S133BF8	BF208	CABGA	С
	70T3319S133BFI	BF208	CABGA	I		70T3339S133BFGI	BFG208	CABGA	I
	70T3319S133BFI8	BF208	CABGA	I		70T3339S133BFI	BF208	CABGA	I
166	70T3319S166BC	BC256	CABGA	С		70T3339S133BFI8	BF208	CABGA	I
	70T3319S166BC8	BC256	CABGA	С	166	70T3339S166BC	BC256	CABGA	С
	70T3319S166BF	BF208	CABGA	С		70T3339S166BC8	BC256	CABGA	С
	70T3319S166BF8	BF208	CABGA	С		70T3339S166BF	BF208	CABGA	С
	70T3319S166BFG	BFG208	CABGA	С		70T3339S166BF8	BF208	CABGA	С
	70T3319S166BFG8	BFG208	CABGA	С	200	70T3339S200BC	BC256	CABGA	С
200	70T3319S200BC	BC256	CABGA	С		70T3339S200BC8	BC256	CABGA	С
	70T3319S200BC8	BC256	CABGA	С		70T3339S200BCG	BCG256	CABGA	С

Orderable Part Information

70T3339/19/99S High-Speed 2.5V 512/256/128K x 18 Dual-Port Static RAM

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70T3399S133BC	BC256	CABGA	С
	70T3399S133BC8	BC256	CABGA	С
	70T3399S133BFI	BF208	CABGA	Ι
	70T3399S133BFI8	BF208	CABGA	Ι
166	70T3399S166BC	BC256	CABGA	С
	70T3399S166BC8	BC256	CABGA	С
200	70T3399S200BC	BC256	CABGA	С
	70T3399S200BC8	BC256	CABGA	С

Orderable Part Information (con't)

Datasheet Document History

01/20/03:	Initial Datasheet
04/25/03:	Page 11 Added Capacitance Derating drawing
	Page 12 Changed tins and ting specs in AC Electrical Characteristics table
11/11/03:	Page 10 Updated power numbers in DC Electrical Characteristics table
	Page 12 Added tops symbol and parameter to AC Electrical Characteristics table
	Page 21 Updated Collision Timing waveform
	Page 22 Added Collision Detection Timing table and footnotes
	Page 26 Updated HIGHZ function in System Interface Parameters table
	Page 27 Added IDT Clock Solution table
04/08/04:	Page 22 & 23 Clarified Sleep Mode Text and Waveforms
	Page 1 & 28 Removed Preliminary status
	Page 6 Added another sentence to footnote 4 to recommend that boundary scan not be operated during sleep mode
02/07/06:	Page 1 Added green availability to features
	Page 7 Changed footnote 2 for Truth Table I from \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = V_{H}$ to \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$
	Page 27 Added green indicator to ordering information
07/28/08:	Page 10 Corrected a typo in the DC Chars table footnotes
01/19/09:	Page 28 Removed "IDT" from orderable part number
04/20/10:	Removed the DD 144-pin TQFP (DD-144) Thin Quad Flatpack per PDN: F-08-01
06/10/15:	Page 3 & 4 Removed the date from all of the pin configurations BC256 & BF208
	Page 26 Added T&R indicator and industrial temp footnote to Ordering Information
02/08/18:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
08/19/19:	Page 2 & 3 Updated package codes BC-256 to BC256, BCG256 and BF-208 to BF208, BFG208
	Page 1, 9, 11 & 26 Removed 166MHz Industrial temp offering
	Page 26 Removed IDT Clock Solution table
	Page 26 & 27 Added Orderable Part Information tables
11/06/19:	Page 26 & 27 Corrected "ns" to "MHz" in the header of the Orderable Part Information tables

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